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Abstract

Method for fabricating a short channel field-effect transistor

The invention relates to a method for fabricating a short channel field-effect transistor, comprising the steps of: forming a sublithographic gate sacrificial layer (3M), forming spacers (7S) at the side walls of the gate sacrificial layer (3M), removing the gate sacrificial layer (3M) to form a gate recess and forming a gate dielectric (10) and a control layer (11) in the gate recess. The result is a short channel FET with minimal fluctuations in the critical dimensions in a range below 100 nanometers.

Figures 1L and 1Q